

# Shinya Yamada

## List of Publications by Year in descending order

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137  
papers

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218381

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138  
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#	ARTICLE	IF	CITATIONS
1	Converse Magnetoelectric Effect in Epitaxial $\text{Co}_{1-x}\text{MnSi}/\text{Pb}(\text{Mg}_{1/3}\text{Nb}_{2/3})\text{O}_3/\text{PbTiO}_3$ Multiferroic Heterostructures. <i>IEEE Transactions on Magnetics</i> , 2022, 58, 1-5.	1.2	3
2	Giant converse magnetoelectric effect in a multiferroic heterostructure with polycrystalline $\text{Co}_2\text{FeSi}$ . <i>NPG Asia Materials</i> , 2022, 14, .	3.8	13
3	Structural insight using anomalous XRD into $\text{Mn}_2\text{CoAl}$ Heusler alloy films grown by magnetron sputtering, IBAS, and MBE techniques. <i>Acta Materialia</i> , 2022, 235, 118063.	3.8	2
4	Epitaxial $\text{Mn}_2\text{VAI}$ films with $\text{Mn}_2\text{VAI}$ films with $\text{Mn}_2\text{VAI}$ structure for all-Heusler stacks. <i>Journal of Magnetism and Magnetic Materials</i> , 2022, , 169644.	1.0	0
5	Half-metallic nature of the low-temperature grown $\text{Co}_2\text{MnSi}$ films on $\text{SrTiO}_3$ . <i>Journal of Alloys and Compounds</i> , 2021, 854, 155571.	2.8	8
6	Experimental estimation of the spin diffusion length in undoped p-Ge on $\text{Fe}_3\text{Si}$ using vertical spin-valve devices. <i>Journal of Applied Physics</i> , 2021, 129, 013901.	1.1	1
7	Positive linear magnetoresistance effect in disordered $\text{Mn}_2\text{VAI}$ epitaxial films. <i>Physical Review B</i> , 2021, 103, .	1.1	15
8	Giant magnetoelectric effect in an $\text{Mn}_2\text{VAI}$ -ordered $\text{Co}_2\text{FeSi}/\text{Pb}(\text{Mg}_{1/3}\text{Nb}_{2/3})\text{O}_3/\text{PbTiO}_3$ multiferroic heterostructure. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	9
9	Room-temperature two-terminal magnetoresistance ratio reaching 0.1% in semiconductor-based lateral devices with $\text{Mn}_2\text{VAI}$ -ordered $\text{Co}_2\text{MnSi}$ . <i>Applied Physics Letters</i> , 2021, 118, .	1.5	16
10	Effect of Fe atomic layers at the ferromagnet-semiconductor interface on temperature-dependent spin transport in semiconductors. <i>Journal of Applied Physics</i> , 2021, 129, .	1.1	5
11	Electric field tunable anisotropic magnetoresistance effect in an epitaxial $\text{Co}_2\text{VAI}$ interfacial multiferroic system. <i>Physical Review Materials</i> , 2021, 5, .	0.9	10
12	Substrate dependent reduction of Gilbert damping in annealed Heusler alloy thin films grown on group IV semiconductors. <i>Applied Physics Letters</i> , 2021, 119, .	1.5	3
13	Superimposed contributions to two-terminal and nonlocal spin signals in lateral spin-transport devices. <i>Physical Review B</i> , 2021, 104, .	1.1	3
14	Magnetoresistance ratio of more than 1% at room temperature in germanium vertical spin-valve devices with $\text{Co}_2\text{FeSi}$ . <i>Applied Physics Letters</i> , 2021, 119, .	1.5	8
15	Control of thermoelectric properties in Mn-substituted $\text{Fe}_3\text{Si}$ epilayers. <i>Physical Review B</i> , 2020, 102, .	1.5	13
16	Suppression of Donor-Driven Spin Relaxation in Strained $\text{Si}$ . <i>Physical Review Applied</i> , 2020, 13, .	1.5	13
17	Germanium pn junctions between ferromagnetic $\text{CoFe}$ and $\text{Fe}_3\text{Si}$ layers for spintronic applications. <i>Materials Science in Semiconductor Processing</i> , 2020, 116, 105066.	1.9	3
18	Inverse local magnetoresistance effect up to room temperature in ferromagnet-semiconductor lateral spin-valve devices. <i>Materials Science in Semiconductor Processing</i> , 2020, 113, 105046.	1.9	2

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19	Spin injection through energy-band symmetry matching with high spin polarization in atomically controlled ferromagnet/ferromagnet/semiconductor structures. NPG Asia Materials, 2020, 12, .	3.8	32
20	Thermoelectric properties of single-phase full-Heusler alloy Fe <sub>2</sub> TiSi films with D <sub>3</sub> -type disordering. Journal of Applied Physics, 2020, 127, .	1.1	12
21	Spin transport in antimony-doped germanium detected using vertical spin-valve structures. Applied Physics Express, 2020, 13, 023001.	1.1	4
22	Growth of ferromagnetic Co <sub>2</sub> FeSi films on flexible Ge(111). Materials Science in Semiconductor Processing, 2020, 112, 104997.	1.9	1
23	Nonmonotonic bias dependence of local spin accumulation signals in ferromagnet/semiconductor lateral spin-valve devices. Physical Review B, 2019, 100, .	1.1	14
24	Great Differences between Low-Temperature Grown Co <sub>2</sub> FeSi and Co <sub>2</sub> MnSi Films on Single-Crystalline Oxides. ACS Applied Electronic Materials, 2019, 1, 2371-2379.	2.0	10
25	Hanle spin precession in a two-terminal lateral spin valve. Applied Physics Letters, 2019, 114, 242401.	1.5	10
26	Magnetic and Transport Properties of Co <sub>1+x</sub> FeV <sub>1-x</sub> Si Epitaxial Films Grown by Molecular Beam Epitaxy. IEEE Transactions on Magnetics, 2019, 55, 1-4.	1.2	1
27	Quantification of Spin Drift in Devices with a Heavily Doped $\text{Si}$ Channel. Physical Review Applied, 2019, 11, .	1.5	12
28	Room-temperature local magnetoresistance effect in n-Ge devices with low-resistive Schottky-tunnel contacts. Applied Physics Express, 2019, 12, 033002.	1.1	11
29	Significant reduction in the thermal conductivity of Si-substituted $\text{Fe}_{1-x}\text{Mn}_x\text{Si}$ epilayers. Physical Review B, 2019, 99, .		
30	Experimental verification of the origin of positive linear magnetoresistance in $\text{CoFe}$ Heusler alloys. Physical Review B, 2019, 100, .	1.1	9
31	Proximity exchange coupling in a Fe/MgO/Si tunnel contact detected by the inverted Hanle effect. Physical Review B, 2019, 100, .	1.1	5
32	Direct observation of pseudo-gap electronic structure in the Heusler-type Fe <sub>2</sub> VAI thin film. Journal of Electron Spectroscopy and Related Phenomena, 2019, 232, 1-4.	0.8	9
33	Anomalous Hall conductivity and electronic structures of Si-substituted $\text{Mn}_2\text{Si}$ epitaxial films. Physical Review B, 2018, 97, .		
34	Effect of Fe <sup>V</sup> nonstoichiometry on electrical and thermoelectric properties of Fe <sub>2</sub> VAI films. Japanese Journal of Applied Physics, 2018, 57, 040306.	0.8	9
35	Magnetic and structural depth profiles of Heusler alloy Co <sub>2</sub> FeAl <sub>0.5</sub> Si <sub>0.5</sub> epitaxial films on Si(100). Journal of Physics Condensed Matter, 2018, 30, 065801.	0.7	3
36	Effect of annealing on the structure and magnetic properties of Co <sub>2</sub> FeAl <sub>0.5</sub> Si <sub>0.5</sub> thin films on Ge(111). Journal of Alloys and Compounds, 2018, 748, 323-327.	2.8	10

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37	Pure spin current transport in a SiGe alloy. Applied Physics Express, 2018, 11, 053006.	1.1	18
38	Nonlinear Electrical Spin Conversion in a Biased Ferromagnetic Tunnel Contact. Physical Review Applied, 2018, 10, .	1.5	21
39	Epitaxial growth of Sb-doped Ge layers on ferromagnetic Fe <sub>3</sub> Si for vertical semiconductor spintronic devices. Semiconductor Science and Technology, 2018, 33, 104008.	1.0	5
40	Observation of local magnetoresistance signals in a SiGe-based lateral spin-valve device. Semiconductor Science and Technology, 2018, 33, 114009.	1.0	12
41	Correlation between spin transport signal and Heusler/semiconductor interface quality in lateral spin-valve devices. Physical Review B, 2018, 98, .	1.1	15
42	Spin transport and relaxation in germanium. Journal Physics D: Applied Physics, 2018, 51, 393001.	1.3	48
43	Spin Absorption Effect at Ferromagnet/Ge Schottky-Tunnel Contacts. Materials, 2018, 11, 150.	1.3	1
44	Modulation of magnetization dynamics in an epitaxial Heusler ferromagnet due to pure spin current in a laterally configured structure. Journal of Physics Condensed Matter, 2018, 30, 255802.	0.7	1
45	Electrical properties of pseudo-single-crystalline Ge films grown by Au-induced layer exchange crystallization at 250°C. Journal of Applied Physics, 2018, 123, 215704.	1.1	24
46	Magnetic and transport properties of equiatomic quaternary Heusler CoFeVSi epitaxial films. Physical Review Materials, 2018, 2, .	0.9	17
47	Electrical properties of epitaxial Lu- or Y-doped La <sub>2</sub> O <sub>3</sub> /La <sub>2</sub> O <sub>3</sub> /Ge high- $k$ gate-stacks. Materials Science in Semiconductor Processing, 2017, 70, 260-264.	1.9	8
48	Low-temperature growth of fully epitaxial CoFe/Ge/Fe <sub>3</sub> Si layers on Si for vertical-type semiconductor spintronic devices. Semiconductor Science and Technology, 2017, 32, 094005.	1.0	17
49	Robust spin-current injection in lateral spin valves with two-terminal Co <sub>2</sub> FeSi spin injectors. AIP Advances, 2017, 7, 055808.	0.6	2
50	Observation of micro-cracks beneath fracture surface during dynamic crack propagation. Theoretical and Applied Fracture Mechanics, 2017, 92, 178-184.	2.1	12
51	Room-temperature spin transport in n-Ge probed by four-terminal nonlocal measurements. Applied Physics Express, 2017, 10, 093001.	1.1	31
52	A crystalline germanium flexible thin-film transistor. Applied Physics Letters, 2017, 111, .	1.5	20
53	Low thermal conductivity of thermoelectric Fe <sub>2</sub> VAl films. Applied Physics Express, 2017, 10, 115802.	1.1	12
54	Spin Transport and Relaxation up to 250ÅK in Heavily Doped n-Type Ge Detected Using Physical Review Applied, 2017, 8, .	1.5	52

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55	Large impact of impurity concentration on spin transport in degenerate n-Ge. Physical Review B, 2017, 95, .	1.1	22
56	Influence of the Ge diffusion on the magnetic and structural properties in Fe <sub>3</sub> Si and CoFe epilayers grown on Ge. Journal of Crystal Growth, 2017, 468, 676-679.	0.7	9
57	Control of electrical properties in Heusler-alloy/Ge Schottky tunnel contacts by using phosphorous $\hat{\Gamma}$ -doping with Si-layer insertion. Materials Science in Semiconductor Processing, 2017, 70, 83-85.	1.9	12
58	Giant Spin Accumulation in Silicon Nonlocal Spin-Transport Devices. Physical Review Applied, 2017, 8, .	1.5	47
59	Electrical detection of spin accumulation and relaxation in $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"} \langle \text{mml:mi} \rangle \text{p} \langle \text{mml:mi} \rangle \langle \text{mml:math} \rangle$ -type germanium. Physical Review Materials, 2017, 1, .	0.9	16
60	Spin signals in Si non-local transport devices with giant spin accumulation. , 2017, , .		1
61	Finely Controlled Approaches to Formation of Heusler-Alloy/Semiconductor Heterostructures for Spintronics. Materials Transactions, 2016, 57, 760-766.	0.4	14
62	Exchange coupling in metallic multilayers with a top FeRh layer. AIP Advances, 2016, 6, .	0.6	4
63	Atomic and electronic structure study of a Co <sub>2</sub> FeAl <sub>0.5</sub> Si <sub>0.5</sub> half-metal thin film on Si(111). Microscopy and Microanalysis, 2016, 22, 1524-1525.	0.2	0
64	Spin transport in $\langle \text{i} \rangle \text{p} \langle \text{i} \rangle$ -Ge through a vertically stacked Ge/Fe <sub>3</sub> Si junction. Applied Physics Letters, 2016, 109, .	1.5	23
65	Realisation of magnetically and atomically abrupt half-metal/semiconductor interface: Co <sub>2</sub> FeSi <sub>0.5</sub> Al <sub>0.5</sub> /Ge(111). Scientific Reports, 2016, 6, 37282.	1.6	18
66	All-epitaxial Co <sub>2</sub> FeSi/Ge/Co <sub>2</sub> FeSi trilayers fabricated by Sn-induced low-temperature epitaxy. Journal of Applied Physics, 2016, 119, .	1.1	17
67	Temperature-independent spin relaxation in heavily doped $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"} \langle \text{mml:mi} \rangle \text{n} \langle \text{mml:mi} \rangle \langle \text{mml:math} \rangle$ -type germanium. Physical Review B, 2016, 94, .	1.1	30
68	The role of chemical structure on the magnetic and electronic properties of Co <sub>2</sub> FeAl <sub>0.5</sub> Si <sub>0.5</sub> /Si(111) interface. Applied Physics Letters, 2016, 108, .	1.5	15
69	Controlling the half-metallicity of Heusler/Si(111) interfaces by a monolayer of Si <sup>δ+</sup> Co <sup>δ-</sup> Si. Journal of Physics Condensed Matter, 2016, 28, 395003.	0.7	3
70	Site-selective nanoscale-polymerization of pyrrole on gold nanoparticles via plasmon induced charge separation. Nanoscale, 2016, 8, 8520-8524.	2.8	31
71	Spin injection into multilayer graphene from highly spin-polarized Co <sub>2</sub> FeSi Heusler alloy. Applied Physics Express, 2016, 9, 063006.	1.1	15
72	(Invited) Finely Controlled Heterointerfaces between Ge(111) and Metallic Alloys or Insulators for Next Generation Ge-Based Devices. ECS Transactions, 2016, 75, 651-659.	0.3	0

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73	Magnetic properties and interfacial characteristics of all-epitaxial Heusler-compound stacking structures. <i>Physical Review B</i> , 2016, 94, .	1.1	4
74	Direct evidence for suppression of the Kondo effect due to pure spin current. <i>Physical Review B</i> , 2016, 94, .	1.1	17
75	A low-temperature fabricated gate-stack structure for Ge-based MOSFET with ferromagnetic epitaxial Heusler-alloy/Ge electrodes. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 063001.	0.8	3
76	Low-temperature and magnetic properties of $B_2$ and $Fe_{100}$ on bcc alloys. <i>Physical Review B</i> , 2015, 92, .	1.1	8
77	Electrical properties of pseudo-single-crystalline germanium thin-film-transistors fabricated on glass substrates. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	44
78	Effect of atomic-arrangement matching on $La_2O_3/Ge$ heterostructures for epitaxial high- $k$ -gate-stacks. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	6
79	A pseudo-single-crystalline germanium film for flexible electronics. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	44
80	Spin-related thermoelectric conversion in lateral spin-valve devices with single-crystalline $Co_2FeSi$ electrodes. <i>Applied Physics Express</i> , 2015, 8, 043003.	1.1	12
81	Reliable reduction of Fermi-level pinning at atomically matched metal/Ge interfaces by sulfur treatment. <i>Applied Physics Letters</i> , 2014, 104, 172109.	1.5	13
82	Improvement of magnetic and structural stabilities in high-quality $Co_2FeSi_{1-x}Al_x/Si$ heterointerfaces. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	34
83	Effect of Sn-doped Ge insertion layers on epitaxial growth of ferromagnetic $Fe_{3-x}Si$ films on a flexible substrate. , 2014, , .		0
84	Large anisotropy of Gilbert damping constant in $L_{21}$ -ordered $Co_2FeSi$ film. <i>Applied Physics Express</i> , 2014, 7, 123001.	1.1	18
85	An All-Epitaxial $Fe_3Si/FeSi/Co_2FeSi$ Trilayer Grown by Room-Temperature Molecular Beam Epitaxy. <i>IEEE Transactions on Magnetics</i> , 2014, 50, 1-3.	1.2	4
86	Formation of Ge(111) on Insulator by Ge epitaxy on Si(111) and layer transfer. <i>Thin Solid Films</i> , 2014, 557, 76-79.	0.8	10
87	A magnetic tunnel junction with an $L_{21}$ -ordered $Co_2FeSi$ electrode formed by all room-temperature fabrication processes. <i>Thin Solid Films</i> , 2014, 557, 386-389.	0.8	7
88	Low-temperature Grown $Ge_{1-x}Sn_x$ layers on a metallic silicide. , 2014, , .		0
89	Atomically controlled heteroepitaxy of Ge on a ferromagnetic heusler alloy for a vertical-type spin transistor. , 2014, , .		0
90	Greatly enhanced generation efficiency of pure spin currents in Ge using Heusler compound $Co_2FeSi$ electrodes. <i>Applied Physics Express</i> , 2014, 7, 033002.	1.1	65

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91	Room-temperature electrical creation of spin accumulation in n-Ge using highly resistive Fe <sub>3</sub> Si/n+-Ge Schottky-tunnel contacts. Thin Solid Films, 2014, 557, 382-385.	0.8	6
92	Uniaxially strained SiGe(111) and SiGe(100) grown on selectively ion-implanted substrates. Journal of Crystal Growth, 2014, 401, 758-761.	0.7	3
93	High-quality Co <sub>2</sub> FeSi <sub>0.5</sub> Al <sub>0.5</sub> /Si heterostructures for spin injection in silicon spintronic devices. Thin Solid Films, 2014, 557, 390-393.	0.8	18
94	Giant enhancement of spin pumping efficiency using Fe <sub>3</sub> Si ferromagnet. Physical Review B, 2013, 88, .	1.1	33
95	Room-temperature sign reversed spin accumulation signals in silicon-based devices using an atomically smooth Fe <sub>3</sub> Si/Si(111) contact. Journal of Applied Physics, 2013, 113, .	1.1	14
96	Room-temperature detection of spin accumulation in silicon across Schottky tunnel barriers using a metal-oxide-semiconductor field effect transistor structure (invited). Journal of Applied Physics, 2013, 113, .	1.1	20
97	Effect of Fe substitution on room-temperature spin polarization in Co <sub>3</sub> Fe <sub>1-x</sub> Si <sub>x</sub> Heusler-compound films. Physical Review B, 2013, 88, .	1.1	14
98	Generation and Detection of a Pure Spin Current Using Co-Based Heusler-Alloy Spin Injector and Detector: Comparison of Co <sub>2</sub> MnSi and Co <sub>2</sub> FeSi. ECS Transactions, 2013, 50, 245-251.	0.3	1
99	Dynamical Spin Injection into p-Type Germanium at Room Temperature. Applied Physics Express, 2013, 6, 023001.	1.1	39
100	(Invited) SiGe Spintronics with Single-Crystalline Ferromagnetic Schottky-Tunnel Contacts. ECS Transactions, 2013, 50, 235-243.	0.3	0
101	Effect of an Atomically Matched Structure on Fermi-level Pinning at Metal/p-Ge Interfaces. ECS Transactions, 2013, 50, 223-229.	0.3	4
102	Lateral spin valves with two-different Heusler-alloy electrodes on the same platform. Applied Physics Letters, 2013, 103, .	1.5	14
103	Qualitative study of temperature-dependent spin signals in n-Ge-based lateral devices with Fe <sub>3</sub> Si/n+-Ge Schottky-tunnel contacts. Journal of Applied Physics, 2013, 113, .	1.1	34
104	An ultra-thin buffer layer for Ge epitaxial layers on Si. Applied Physics Letters, 2013, 102, .	1.5	22
105	Ion beam analysis of quaternary Heusler alloy Co <sub>2</sub> (Mn <sub>1-x</sub> Fe <sub>x</sub> )Si(111) epitaxially grown on Ge(111). Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1828-1831.	0.8	0
106	Room-Temperature Tunneling Magnetoresistance in Magnetic Tunnel Junctions with a DO <sub>3</sub> -Fe <sub>3</sub> Si Electrode. Japanese Journal of Applied Physics, 2013, 52, 04CM02.	0.8	10
107	Molecular Beam Epitaxy of Co <sub>2</sub> MnSi Films on Group-IV Semiconductors. Japanese Journal of Applied Physics, 2013, 52, 04CM06.	0.8	14
108	Temperature evolution of spin accumulation detected electrically in a nondegenerated silicon channel. Physical Review B, 2012, 85, .	1.1	31

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109	Estimation of the spin polarization for Heusler compound thin films by means of nonlocal spin-valve measurements: Comparison of Co <sub>2</sub> FeSi and Fe <sub>3</sub> Si. Physical Review B, 2012, 85, .	1.1	81
110	Room-temperature generation of giant pure spin currents using epitaxial Co <sub>2</sub> FeSi spin injectors. NPG Asia Materials, 2012, 4, e9-e9.	3.8	86
111	Effect of Addition of Al to Single-Crystalline CoFe Electrodes on Nonlocal Spin Signals in Lateral Spin-Valve Devices. Applied Physics Express, 2012, 5, 063004.	1.1	18
112	Room-temperature structural ordering of a Heusler compound Fe <sub>3</sub> Si. Physical Review B, 2012, 86, .	1.1	48
113	Effect of the magnetic domain structure in the ferromagnetic contact on spin accumulation in silicon. Applied Physics Letters, 2012, 101, 232404.	1.5	6
114	Atomically Controlled Epitaxial Growth of Single-Crystalline Germanium Films on a Metallic Silicide. Crystal Growth and Design, 2012, 12, 4703-4707.	1.4	37
115	Sign determination of spin polarization in Co <sub>2</sub> FeSi using a Pt-based spin Hall device. Physical Review B, 2012, 86, .	1.1	8
116	Spin accumulation created electrically in an n-type germanium channel using Schottky tunnel contacts. Journal of Applied Physics, 2012, 111, .	1.1	62
117	Influence of Al co-deposition on the crystal growth of Co-based Heusler-compound thin films on Si(111). Thin Solid Films, 2012, 520, 3419-3422.	0.8	12
118	Electric-field control of spin accumulation signals in silicon at room temperature. Applied Physics Letters, 2011, 99, 132511.	1.5	56
119	Mechanism of Fermi level pinning at metal/germanium interfaces. Physical Review B, 2011, 84, .	1.1	32
120	Local structural ordering in low-temperature-grown epitaxial Fe <sub>3</sub> Si. Physical Review B, 2011, 84, .	1.1	51
121	Low-temperature-grown quaternary Heusler-compound Co <sub>2</sub> Mn <sup>2+</sup> Fe <sub>x</sub> Si films on Ge(111). Journal of Applied Physics, 2011, 109, 07B113.	1.1	25
122	Epitaxial growth of a full-Heusler alloy Co <sub>2</sub> FeSi on silicon by low-temperature molecular beam epitaxy. Thin Solid Films, 2010, 518, S278-S280.	0.8	19
123	Validation of stepwise refinement with test cases generated from formal specification. , 2010, , .		1
124	High-quality ferromagnetic CoFe/Si contacts for Si spin-transistor applications. , 2010, , .		1
125	Significant growth-temperature dependence of ferromagnetic properties for Co <sub>2</sub> FeSi/Si(111) prepared by low-temperature molecular beam epitaxy. Applied Physics Letters, 2010, 96, .	1.5	65
126	High-quality epitaxial CoFe/Si(111) heterostructures fabricated by low-temperature molecular beam epitaxy. Applied Physics Letters, 2010, 97, .	1.5	28



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127	Ferromagnetic Co <sub>3</sub> Fe <sub>x</sub> /Si/Si(111) contacts with high-quality heterointerfaces for spin-transistor applications. , 2010, , .		0
128	Highly ordered Co <sub>2</sub> FeSi Heusler alloys grown on Ge(111) by low-temperature molecular beam epitaxy. Journal of Applied Physics, 2010, 107, .	1.1	44
129	Mid-infrared pulsed laser lithotripsy using an Er:YAG laser and a difference frequency generation laser. Proceedings of SPIE, 2008, , .	0.8	1
130	Magnetic field effects on photoelectrochemical reactions of modified electrodes with C60-phenothiazine nanoclusters. Science and Technology of Advanced Materials, 2006, 7, 643-648.	2.8	15
131	A novel laser angioplasty guided hollow fiber using mid-infrared laser. , 2006, , .		0
132	Photoinduced intramolecular electron-transfer reactions in carbazole-fullerene and phenothiazine-fullerene linked compounds in benzene and benzonitrile as studied by fluorescence, transient absorption, time-resolved EPR, and magnetic field effects. Applied Magnetic Resonance, 2003, 23, 289-307.	0.6	24
133	Inner Approximation Method for a Reverse Convex Programming Problem. Journal of Optimization Theory and Applications, 2000, 107, 355-389.	0.8	5
134	Facile oxidation of thiophenol by a flavin immobilized in cationic polyelectrolytes: A flavoenzyme model. Journal of Polymer Science, Polymer Letters Edition, 1978, 16, 137-140.	0.4	9
135	Construction of a consulting system from structural description of a mechanical object. , 0, , .		7
136	Manipulator control by using servoing with the stereo vision. , 0, , .		13
137	An inner approximation method for a reverse convex programming problem. , 0, , .		1